

AUTOMOTIVE CURRENT TRANSDUCER HAH1BV S/04





Introduction

The HAH1BV family is for use on the electronic measurement of DC, AC or pulsed currents in high power automotive applications with a galvanic isolation between the primary circuit (high power) and the secondary circuit (electronic circuit)

The HAH1BV family gives you the choice of having different current measuring ranges in the same housing (from \pm 200 A up to \pm 900 A).

Features

- Open Loop transducer using the Hall effect
- Unipolar + 5 V DC power supply
- Primary current measuring range up to ± 700 A
- Maximum rms primary admissible current: defined by busbar to have T° < + 150°C
- Operating temperature range: 40°C < T° < + 125°C
- Output voltage: full ratio-metric (in gain and offset)
- Compact design.

Advantages

- Excellent accuracy
- Very good linearity
- Very low thermal offset drift
- Very low thermal gain drift
- Wide frequency bandwidth
- No insertion losses.

Automotive applications

- Battery monitoring
- Starter Generators
- Inverters
- HEV application
- EV application.

Principle of HAH1BV Family

The open loop transducers use an Hall effect integrated circuit.

The magnetic flux density B, contributing to the rise of the Hall voltage, is generated by the primary current $\rm I_{\rm p}$ to be measured.

The current to be measured $I_{\rm p}$ is supplied by a current source i.e. battery or generator (Fig. 1).

Within the linear region of the hysteresis cycle, B is proportional to:

B
$$(\mathbf{I}_{P})$$
 = constant (a) x \mathbf{I}_{P}

The Hall voltage is thus expressed by:

 \mathbf{V}_{H} = (R_H/d) x I x constant (a) x I_P

Except for $\mathbf{I}_{_{\!\mathrm{P}}}\!\!,$ all terms of this equation are constant. Therefore:

 V_{μ} = constant (b) x I_{p}

The measurement signal $\mathbf{V}_{_{\rm H}}$ amplified to supply the user output voltage or current.



Fig. 1: Principle of the open loop transducer



Dimensions HAH1BV family (in mm. 1mm = 0.0394 inch)



3 ±0.1

0.15

8.0.1 10.1



Bill of materials

Right view

Plastic case
Plastic case

PBT GF 30

Π

<u>Ø2.5</u> ±0.1

32.25 ±0.5

- Magnetic core Iron silicon alloyPins Brass tin platted
- Weight 39 g

Remarks

• $V_{OUT} > \frac{V_c}{2}$ when I_p flows in the direction of the arrow.

System artitecture



System architecture (example)

 $\mathbf{R}_{_{\rm I}}$ > 10 k Ω optional resistor for signal line diagnostic

V _{OUT}	Diagnosis
Open circuit	$\mathbf{V}_{\text{IN}} = \mathbf{V}_{\text{C}}$
Short GND	V _{IN} = OV

 C_{I} < 100 nF EMC protection

RC Low pass filter EMC protection (optional)





Absolute maximum ratings

	Symbol	Unit	Specification			O an differen
	Symbol	bol Unit	Min	Тур	Max	Conditions
Electrical Data						
Max primary current peak	I _{Pmax}	A			1)	
Supply continuous over voltage					8.5	
Supply over voltage	V _c	V			14	1 min
Reverse voltage			-14			1 min @ T _A = 25°C
Output over voltage (continuous)	V _{OUT}	V			8.5	
Output over voltage					14	1 min @ T _A = 25°C
Continuous output current	I _{out}	mA	-10		10	
Output short-circuit duration	T _c	min			2	
Rms voltage for AC isolation test	V _d	kV			2	50 Hz, 1 min
Isolation resistance	R _{IS}	MΩ	500			500 V - ISO 16750-2
Electrostatic discharge voltage	V	kV			2	JESD22-A114-B
Ambient storage temperature	Ts	°C	-40		125	

Operating characteristics

	Symbol	Unit		Specificatio	n	Conditions
	Symbol	Unit	Min	Тур	Max	Conditions
			Electrica	l Data		
Primary current	I _p	A	-700		700	
Calibration current	I _{CAL}	А	-500		500	@ T _A = 25°C
Supply voltage	V _c	V	4.5	5.00	5.5	
Output voltage	V _{OUT}	V	V _{out} =	(V _c /5) x (2.5 ·	+ G X I _P)	@ V _c
Sensitivity 2)	G	mV/A		2.86		@ V _c = 5 V
Current consumption		mA		7	10	@ $V_c = 5 V$, - 40°C < $T_A < 125$ °C
Power up inrush current	I _c	mA			15	@ V _c < 3.5 V
Load resistance	RL	ΚΩ	10			
Output internal resistance	R _{OUT}	Ω			10	
Capacitive loading	C	nF	1		100	
Ambient operating temperature	T _A	°C	-40		125	
Output drift versus power supply		%	-1	0.3	1	
			Performan	ce Data		
Sensitivity error	8,0	%	-1.0	± 0.5	1.0	@ T _A = 25°C, '@ V _C = 5 V
Electrical offset current	I _{OE}	A		± 1.7		$@ T_{A} = 25^{\circ}C, @ V_{C} = 5 V$
Magnetic offset current	I _{om}	А		± 1.2		@ $T_{A} = 25^{\circ}C$, '@ $V_{C} = 5 \text{ V after } \pm I_{P}$
	I _o	А		± 2.9		
Globale offset current			-4.3		4.3	@ T _A = 25°C
Average temperature coefficient of $\mathbf{V}_{_{\mathrm{OE}}}$	TCV	mV/°C	-0.06	± 0.02	0.06	@ - 40°C < T _A < 125°C
Average temperature coefficient of G	TCG _{AV}	%/°C	-0.04	± 0.02	0.04	@ - 40°C < T _A < 125°C
Linearity error	£,	%	-1.0		1.0	of full range
Response time to 90 % of I _{PN} step	t,	ms			5	@ di/dt = 50 A/µs
Frequency bandwidth	BW	Hz			80	@ -3 dB
Output clamping min voltage	V _{sz}	V	0.24	0.25	0.26	@ V _c = 5 V
Output clamping max voltage	V _{sz}	V	4.74	4.75	4.76	@ V _c = 5 V
Output voltage noise peak peak	V no pp	mV	-		10	
Resolution		mV		2.5		@ V _c = 5 V
Power up time		ms		25	100	-
Setting time after overload		ms			25	

Notes:

¹⁾ Busbar temperature must be below 150°C. ²⁾ The output voltage V_{OUT} is fully ratio-metric, that concerns V_O , **G**, it depends on the supply voltage V_C in relative with the following formula:

$$I_{\text{P}} = \left(V_{\text{out}} - \frac{V_{\text{c}}}{2}\right) \times \frac{1}{G} \times \frac{5}{V_{\text{c}}} \qquad \text{with } G \text{ in } (V \,/\, A)$$

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5 4 3 2 1 0 -1 -2 -3 -4 -5 -40 -20 0 20 40 60 80 100 120 Temperature (°C)





HAH1BV S/04 Frequency Bandwith





120 100 80 € 60 40 20 0 -5 0 5 10 15 20 25 30 Time (ms)

HAH1BV S/04 Phase



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PERFORMANCES PARAMETERS DEFINITIONS

Output noise voltage:

The output voltage noise is the result of the noise floor of the Hall elements and the linear I_c amplifier gain.

Magnetic offset:

The magnetic offset is the consequence of an over-current on the primary side. It's defined after an excursion of ${\rm I}_{\rm P\,max}$

Linearity:

The maximum positive or negative discrepancy with a reference straight line V_{_{\rm OUT}} = f (I__).

Unit: linearity (%) expressed with full scale of $I_{p max}$. Linearity is measured on cycle + I_{p} , O, - I_{p} , O, + I_{p} without magnetic offset (average values used)



Response time (delay time) t,:

The time between the primary current signal and the output signal reach at 90 % of its final value



Typical:

Theorical value or usual accuracy recorded during the production.

Sensitivity:

The Transducer's sensitivity **G** is the slope of the straight line $V_{out} = f(I_p)$, it must establish the relation: $V_{out}(I_p) = V_c/5$ (G x $I_p + 2.5$) (*) (*) For all symetrics transducers.

Offset with temperature:

The error of the offset in the operating temperature is the variation of the offset in the temperature considered with the initial offset at 25° C.

The offset variation $\mathbf{I}_{_{OT}}$ is a maximum variation the offset in the temperature range:

 $I_{OT} = I_{OF} \max - I_{OF} \min$

The Offset drift $\textbf{TCI}_{\text{DEAV}}$ is the \textbf{I}_{DT} value divided by the temperature range.

Sensitivity with temperature:

The error of the sensitivity in the operating temperature is the relative variation of sensitivity with the temperature considered with the initial offset at 25°C.

The sensitivity variation \mathbf{G}_{T} is the maximum variation (in ppm or %) of the sensitivity in the temperature range:

 \mathbf{G}_{τ} = (Sensitivity max - Sensitivity min) / Sensitivity at 25°C.

The sensitivity drift \textbf{TCG}_{AV} is the \textbf{G}_{T} value divided by the temperature range.

Offset voltage @ $I_p = 0 A$:

Is the output voltage when the primary current is null. The ideal value of $V_{\rm o}$ is $V_{\rm c}/2$ at $V_{\rm c}$ = 5 V. So, the difference of $V_{\rm o}$ - $V_{\rm c}/2$ is called the total offset voltage error. This offset error can be attributed to the electrical offset (due to the resolution of the ASIC quiescent voltage trimming), the magnetic offset, the thermal drift and the thermal hysteresis.

Environmental test specifications

Name	Standard	Conditions	
Damp heat, steady state	JESD22-A101	85°C - 85°C / 1000h	
Isolation resistance	ISO 16750-2 § 4.10	500 V/1min	
Temperature humidity cycle test	ISO 16750-4	-10 + 85°C 10 days	
Isolation test	IEC 60664-1	2 kV/50 Hz/1min	
Mechanical tests			
Vibration test (random)	IEC 60068-2-64 ISO 16750-3 & 4.1.6.1.6	20 2000 Hz Random rms (11g rms) 8h/axis	
Terminal strength test	According to LEM		
Thermal shocks	IEC 60068-214 Na	-40 + 125°C 300 cycles	
Free fall	ISO 16750-3 § 4.3	1m concrete ground	
EMC Test			
Radiated electronagnetic immunity	Directive 2004/104/CE ISO 11452-2	30 V/m 20-2000 MHz	
Bulk current injection immunity	Directive 2004/104/CE ISO 11452-4	1-400 MHz	
Radiated radio frequency electromagnetic field immunity	IEC 61000-4-3	80000 MHz-10V/m	
Electrostatic discharge immunity test	IEC 61000-4-2	Air discharge=2 kV	

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